

N-CHANNEL SILICON POWER MOS-FET

F-II SERIES

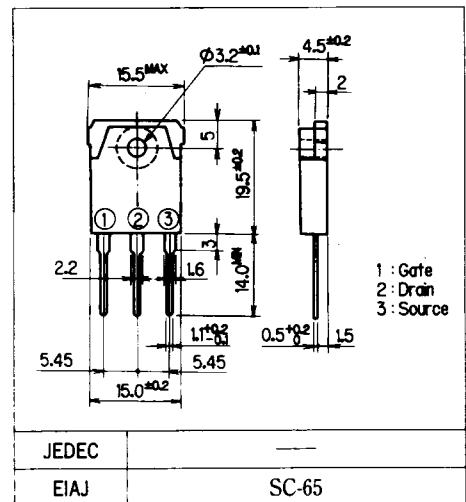
Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage
- $V_{GSS} = \pm 30V$ Guarantee

Applications

- Switching regulators
- UPS
- DC-DC converters
- General purpose power amplifier

Outline Drawings

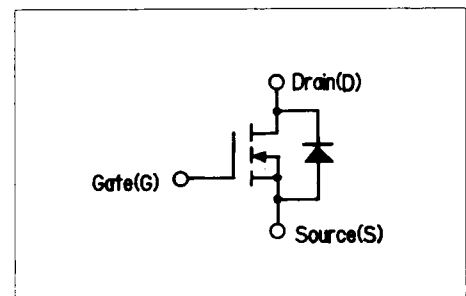


Max. Ratings and Characteristics

Absolute Maximum Ratings($T_c = 25^\circ C$) :

Items	Symbols	Ratings	Units
Drain-source voltage	V_{DSS}	900	V
Continuous drain current	I_D	8	A
Pulsed drain current	$I_{D(puls)}$	23	A
Continuous reverse drain current	I_{DR}	8	A
Gate-source peak voltage	V_{GSS}	± 30	V
Max. power dissipation	P_D	150	W
Operating and storage temperature range	T_{ch} T_{stg}	150 $-55 \sim +150$	$^\circ C$ $^\circ C$

Equivalent Circuit Schematic



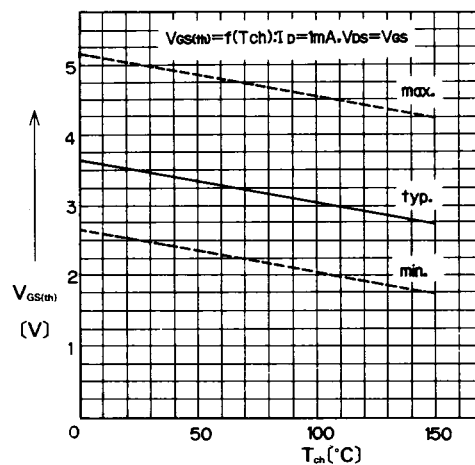
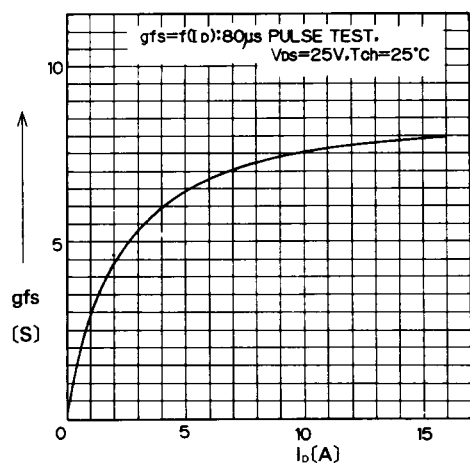
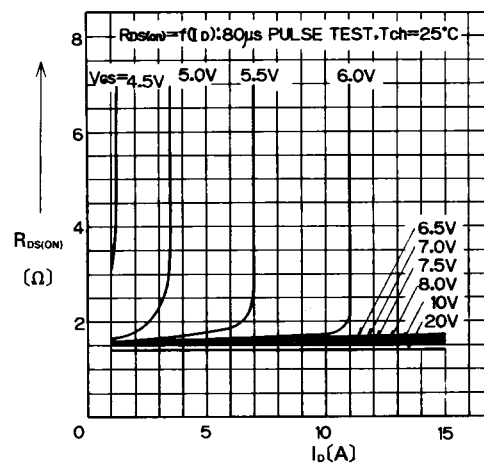
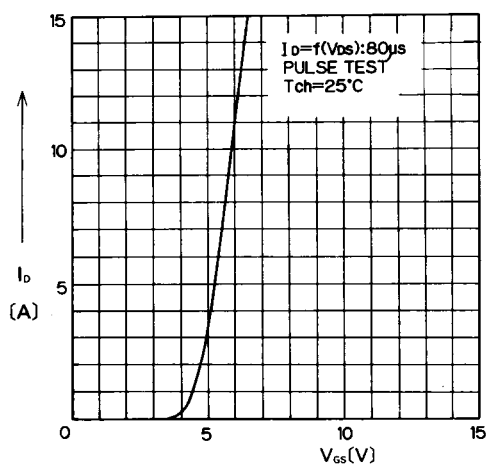
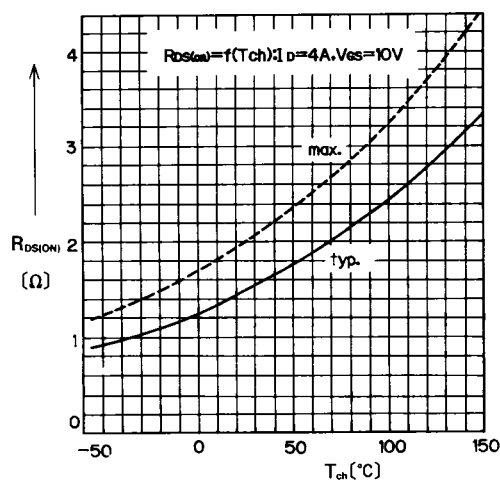
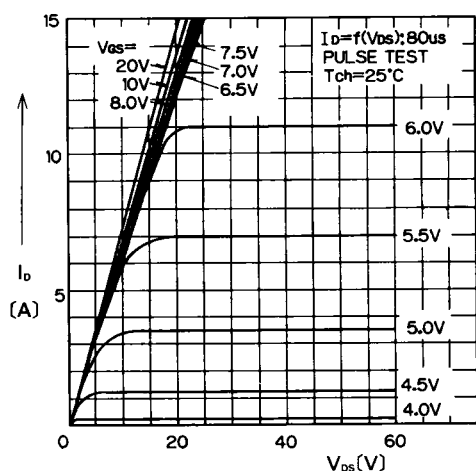
Electrical Characteristics($T_c = 25^\circ C$)

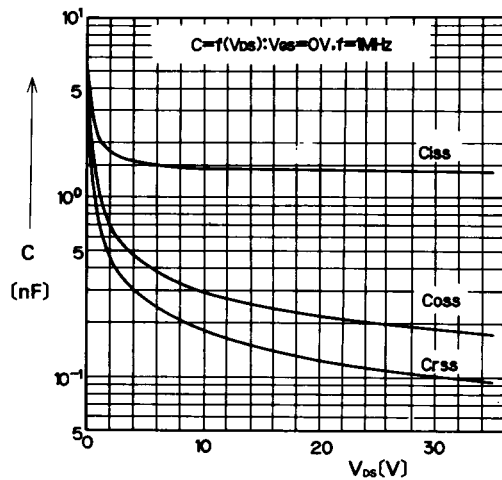
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1mA$ $V_{GS} = 0V$	900			V
Gate threshold voltage	$V_{GS(th)}$	$I_D = 1mA$ $V_{DS} = V_{GS}$	2.5	3.5	5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 900V$ $V_{GS} = 0V$ $T_{ch} = 25^\circ C$		10	500	μA
		$T_{ch} = 125^\circ C$		0.2	1.0	mA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 30V$ $V_{DS} = 0V$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 4A$ $V_{GS} = 10V$		1.48	2.0	Ω
Forward transconductance	g_{fs}	$I_D = 4A$ $V_{DS} = 25V$	3.0	6.0		S
Input capacitance	C_{iss}	$V_{DS} = 25V$		1400	2100	pF
Output capacitance	C_{oss}	$V_{GS} = 0V$		200	300	
Reverse transfer capacitance	C_{rss}	$f = 1MHz$		110	160	
Turn-on time t_{on} ($t_{on} + t_{d(on)} + t_r$)	$t_{d(on)}$	$V_{CC} = 600V$ $I_D = 8A$ $V_{GS} = 10V$ $R_G = 25\Omega$		50	75	ns
	t_r			230	350	
Turn-off time t_{off} ($t_{d(off)} + t_f$)	$t_{d(off)}$			300	450	
	t_f			160	240	
Diode forward on-voltage	V_{SD}	$I_F = 2 \times I_{DR}$ $V_{GS} = 0V$ $T_{ch} = 25^\circ C$		1.0	1.5	V
Reverse recovery time	t_{rr}	$I_F = I_{DR}$ $dI/dt = 100A/\mu s$ $T_{ch} = 25^\circ C$		1000		ns

Thermal Characteristics

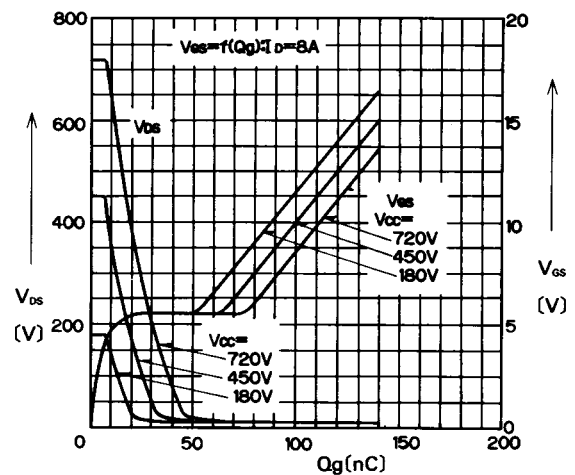
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(ch-a)}$	channel to air			35.0	$^\circ C/W$
	$R_{th(ch-c)}$	channel to case			0.83	$^\circ C/W$

Characteristics

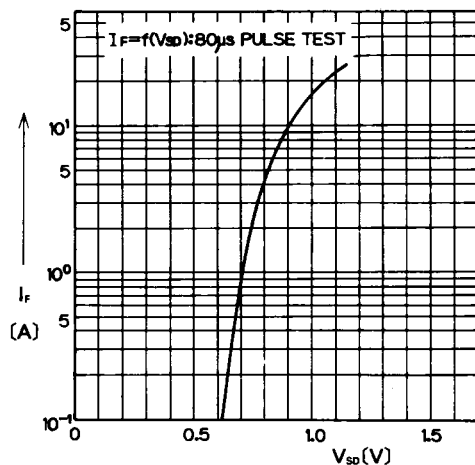




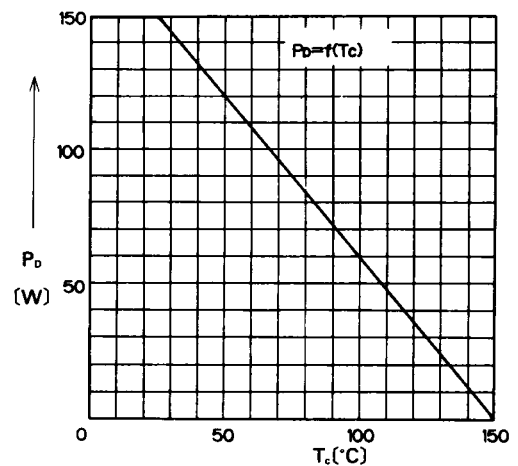
Typical Capacitance vs. V_{DS}



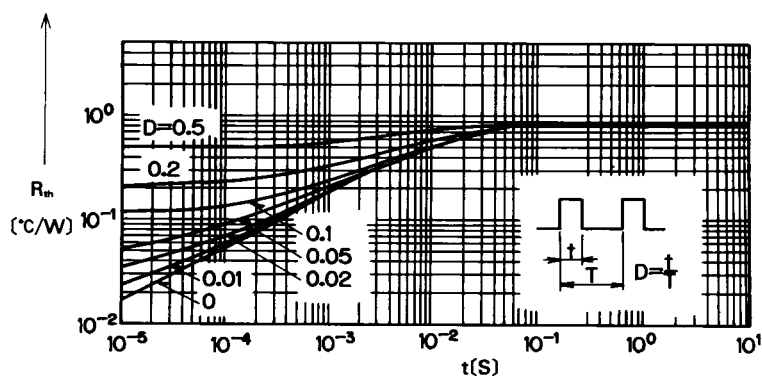
Typical Input Charge



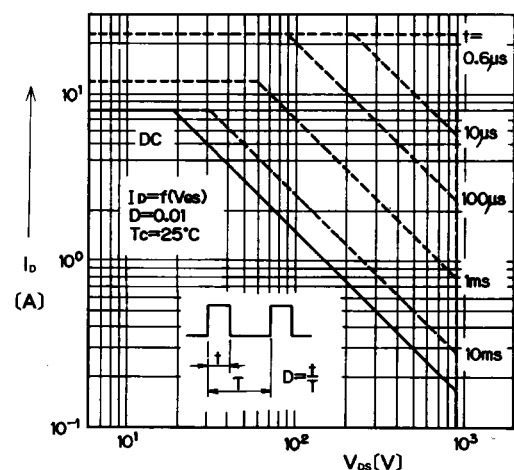
Forward Characteristics of Reverse Diode



Allowable Power Dissipation vs. T_c



Transient Thermal Impedance



Safe Operating Area